1. General description

NPN low V_{CEsat} transistor in a medium power SOT89 (SC-62) package.

PNP complement: PBSS5540X.

2. Features and benefits

- High h_{FE} and low V_{CEsat} at high current operation
- High collector current capability: I_C maximum 4 A
- High efficiency leading to less heat generation.
- AEC-Q101 qualified

3. Applications

- Medium power peripheral drivers (e.g. fan and motor)
- · Strobe flash units for DSC and mobile phones
- Inverter applications (e.g. TFT displays)
- · Power switch for LAN and ADSL systems
- Medium power DC-to-DC conversionc
- Battery chargers.

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	40	V
Ic	collector current		-	-	4	Α
I _{CM}	peak collector current	single pulse; t _p ≤ 10 ms	-	-	10	Α
R _{CEsat}	collector-emitter saturation resistance	I_C = 5 A; I_B = 500 mA; $t_p \le 300$ μs; pulsed; δ ≤ 0.02; T_{amb} = 25 °C	-	40	71	mΩ



40 V, 5 A NPN low VCEsat (BISS) transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter		С
2	С	collector		
3	В	base	3 2 1	В — , , , , , , , , , , , , , , , , , , ,
			SOT89	sym123

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PBSS4540X		plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body	SOT89			

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBSS4540X	%1B

[1] % = placeholder for manufacturing site code

40 V, 5 A NPN low VCEsat (BISS) transistor

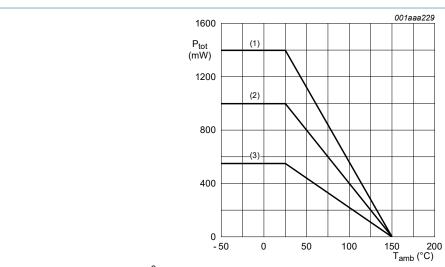
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	40	V
V _{CEO}	collector-emitter voltage	open base		-	40	V
V _{EBO}	emitter-base voltage	open collector		-	6	V
I _C	collector current			-	4	Α
I _{CRM}	repetitive peak collector current	$\delta \le 0.02; t_p \le 10 \text{ ms}$	[1]	-	5	А
I _{CM}	peak collector current	single pulse; t _p ≤ 10 ms		-	10	Α
I _B	base current			-	1	Α
I _{BM}	peak base current	single pulse; t _p ≤ 1 ms		-	2	Α
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1] [2]	-	2.5	W
			[1]	-	0.55	W
			[3]	-	1	W
			[4]	-	1.4	W
			[5]	-	1.6	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] [3] Operated under pulsed conditions; $t_p \le 10$ ms; $\delta \le 0.2$.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm²
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- Device mounted on a 7 cm² ceramic PCB, 1 cm² single-sided copper and tin-plated. [5]



- (1) FR4 PCB; 6 cm² mounting pad for collector (2) FR4 PCB; 1 cm² mounting pad for collector
- (3) FR4; standard footprint

Power derating curves Fig. 1.

40 V, 5 A NPN low VCEsat (BISS) transistor

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$R_{\text{th(j-a)}}$	thermal resistance from	in free air [1] [2 [1] [3] [4] [5]	[1] [2]	-	-	50	K/W
	junction to ambient		[1]	-	-	225	K/W
			[3]	-	-	125	K/W
			[4]	-	-	90	K/W
			[5]	-	-	80	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	16	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Operated under pulsed conditions; $t_p \le 10$ ms; $\delta \le 0.2$.
- [3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm²
- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².
- [5] Device mounted on a 7 cm² ceramic PCB, 1 cm² single-sided copper and tin-plated.

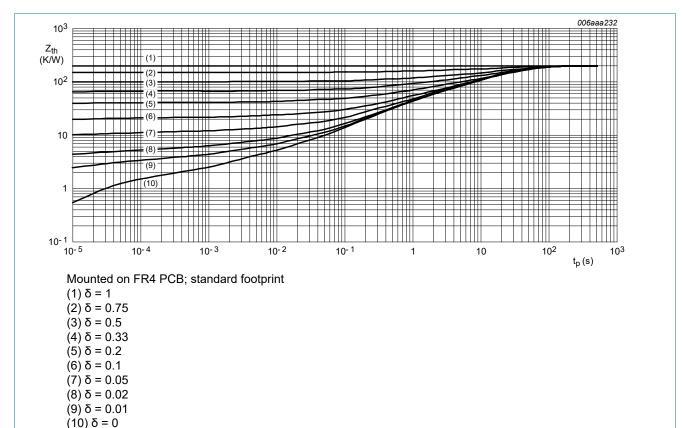


Fig. 2. Transient thermal impedance as a function of pulse duration; typical values

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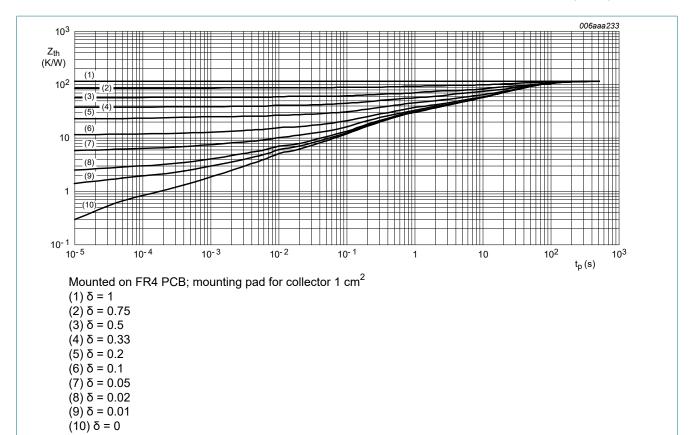
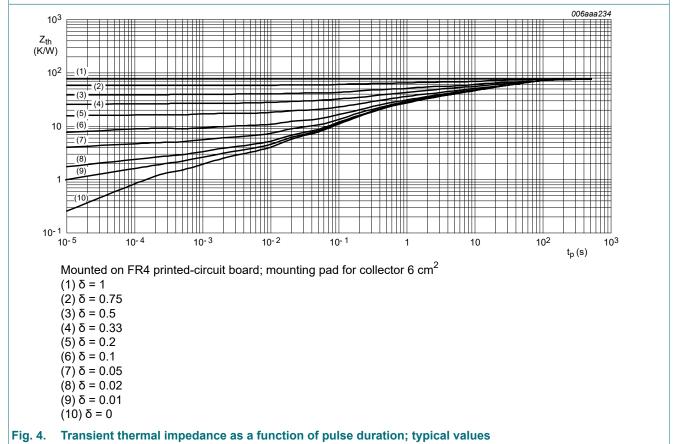


Fig. 3. Transient thermal impedance as a function of pulse duration; typical values



40 V, 5 A NPN low VCEsat (BISS) transistor

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CBO}	collector-base cut-off	V _{CB} = 30 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 30 V; I _E = 0 A; T _j = 150 °C	-	-	50	μΑ
I _{CES}	collector-emitter cut-off current	V _{CE} = 30 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
h _{FE}	DC current gain	V _{CE} = 2 V; I _C = 0.5 A; T _{amb} = 25 °C	300	-	-	
		V_{CE} = 2 V; I_{C} = 1 A; $t_{p} \le 300 \ \mu s$; pulsed; $\delta \le 0.02$; T_{amb} = 25 °C	300	-	-	
		V_{CE} = 2 V; I_{C} = 2 A; $t_{p} \le 300 \ \mu s$; pulsed; $\delta \le 0.02$; T_{amb} = 25 °C	250	-	-	
		V_{CE} = 2 V; I_{C} = 5 A; $t_{p} \le 300 \ \mu s$; pulsed; $\delta \le 0.02$; T_{amb} = 25 °C	100	-	-	
V _{CEsat}	collector-emitter saturation voltage	I _C = 0.5 A; I _B = 5 mA; T _{amb} = 25 °C	-	-	90	mV
		I _C = 1 A; I _B = 10 mA; T _{amb} = 25 °C	-	-	120	mV
		I_C = 2 A; I_B = 200 mA; $t_p \le 300$ μs; pulsed; $\delta \le 0.02$; T_{amb} = 25 °C	-	-	150	mV
		I_C = 4 A; I_B = 200 mA; $t_p \le 300$ μs; pulsed; $\delta \le 0.02$; T_{amb} = 25 °C	-	-	290	mV
		$I_C = 5 \text{ A}; I_B = 500 \text{ mA}; t_p \le 300 \text{ µs};$	-	-	355	mV
R _{CEsat}	collector-emitter saturation resistance	pulsed; δ ≤ 0.02; T _{amb} = 25 °C	-	40	71	mΩ
V _{BEsat}	base-emitter saturation voltage	I_C = 4 A; I_B = 200 mA; $t_p \le 300$ μs; pulsed; $\delta \le 0.02$; T_{amb} = 25 °C	-	-	1.1	V
		I_C = 5 A; I_B = 500 mA; $t_p \le 300$ μs; pulsed; $\delta \le 0.02$; T_{amb} = 25 °C	-	-	1.2	V
V_{BEon}	base-emitter turn-on voltage	V_{CE} = 2 V; I_{C} = 2 A; $t_{p} \le 300 \ \mu s$; pulsed; $\delta \le 0.02$; T_{amb} = 25 °C	-	-	1.1	V
f⊤	transition frequency	$V_{CE} = 10 \text{ V}; I_{C} = 0.1 \text{ A}; f = 100 \text{ MHz};$ $T_{amb} = 25 \text{ °C}$	70	-	-	MHz
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25 ^{\circ}\text{C}$	-	-	75	pF

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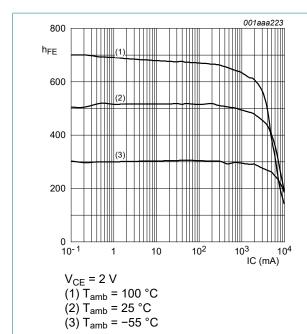


Fig. 5. DC current gain as a function of collector current; typical values

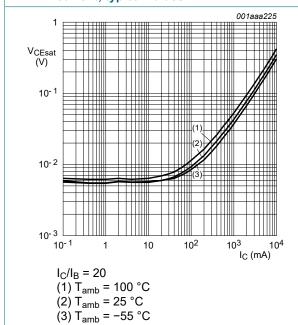


Fig. 7. Collector-emitter saturation voltage as a function of collector current; typical values

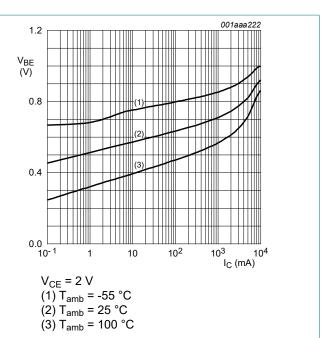


Fig. 6. Base-emitter voltage as a function of collector current; typical values

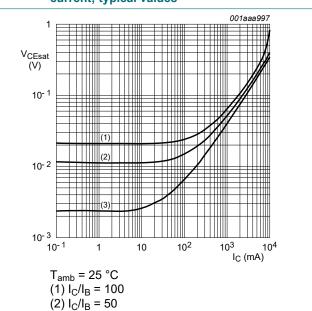


Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

(3) $I_C/I_B = 10$

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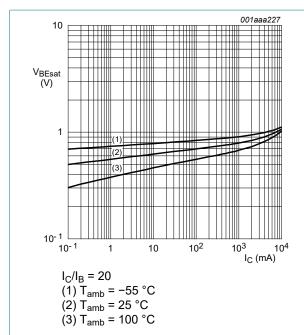
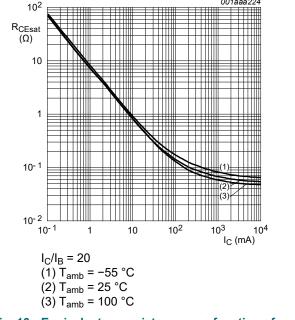
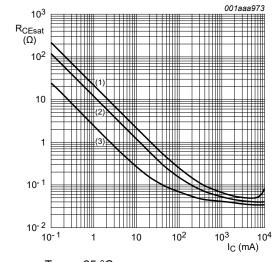


Fig. 9. collector current; typical values

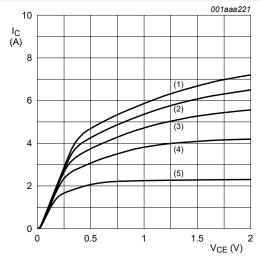


Base-emitter saturation voltage as a function of Fig. 10. Equivalent on-resistance as a function of collector current; typical values



T_{amb} = 25 °C (1) $I_C/I_B = 100$ (2) $I_C/I_B = 50$ (3) $I_{\rm C}/I_{\rm B} = 10$

Fig. 11. Equivalent on-resistance as a function of collector current; typical values

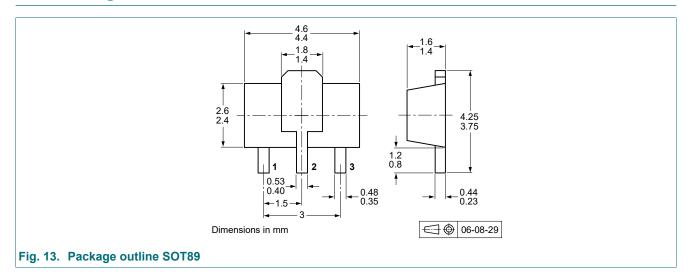


(1) $I_B = 25 \text{ mA}$ (2) $I_B = 20 \text{ mA}$ (3) $I_B = 15 \text{ mA}$ (4) $I_B = 10 \text{ mA}$ (5) $I_B = 5 \text{ mA}$

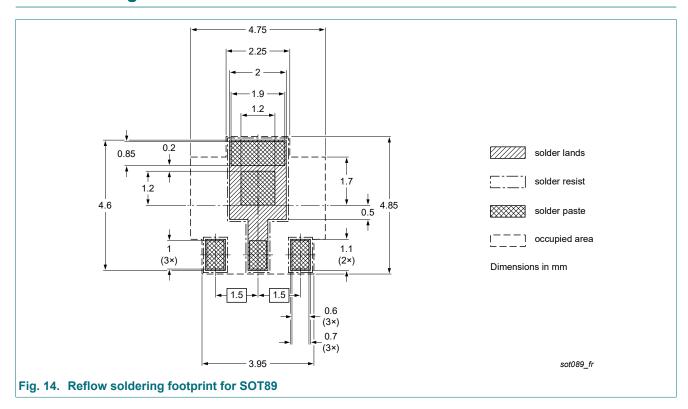
Fig. 12. Collector current as a function of collectoremitter voltage; typical values

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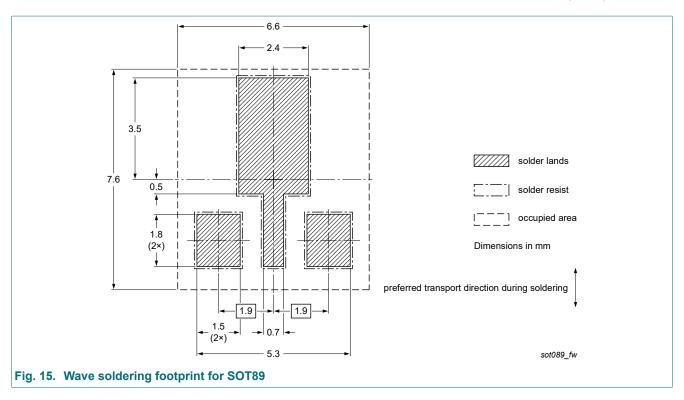
11. Package outline



12. Soldering



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13. Revision history

Table 8. Revision history

	7.0.7			
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4540X v.3	20200415	Product data sheet	-	PBSS4540X v.2
Modifications:	Nexperia. Legal texts have Limiting values a	s data sheet has been rede been adapted to the new cat I _{CM} : conditions corrected at figure 6: legend corrected	ompany name where a	, ,
PBSS4540X v.2	20041104	Product data sheet	-	PBSS4540X v.1
PBSS4540X v.1	20040611	Product data sheet	-	-

40 V, 5 A NPN low VCEsat (BISS) transistor

14. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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Date of release: 15 April 2020

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